

Current-voltage characteristics of a tunnel junction with resonant centers

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Abstract

We calculate the I-V characteristics of a tunnel junction containing impurities in the barrier. We consider the indirect resonant tunneling involving the impurities. The Coulomb repulsion energy E_c between two electrons with opposite spins simultaneously residing on the impurity is introduced by an Anderson Hamiltonian. At low temperatures $T \ll E_c$ the I-V characteristic is linear in V both for $V < E_c$ and for $V > E_c$ and changes slope at $V = E_c$. This behavior reflects the energy spectrum of the impurity electrons - the finite value of the charging energy E_c . At $T \sim E_c$ the junction reveals an ohmic-like behavior as a result of the smearing out of the charging effects by the thermal fluctuations.

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In this paper, we study the transport through a tunnel junction with a thin, amorphous insulating layer separating the metal leads. At low temperatures two tunneling channels contribute to the conductance. The first one is the direct tunneling between the leads. The second one is a resonant tunneling through impurity states present in the barrier. This mechanism is dominant for not too small thickness of the layer [1,2]. For higher temperatures and larger applied voltages the inelastic tunneling involving pairs of localized states with phonon emission or absorption becomes important [3–5]. We restrain our study to the case of resonant tunneling and calculate the current-voltage characteristics of such junctions. The current flows through the junction by tunneling of electrons from the emitter electrode to the impurity and then to the collector. We calculate the tunneling current through the impurity by taking into account the Coulomb repulsion energy between two electrons with opposite spins simultaneously residing on the localized state. In systems such as *a-Si* tunnel junctions this energy is rather large ($0.1 - 0.2$ eV) [5,6]. Experimentally measured current for a given *dc* voltage bias is obtained by averaging the currents through the individual impurities over their positions and energy distribution.

The Hamiltonian of the system under consideration consists of three terms:

$$H_{tot} = H_{leads} + H_{imp} + H_{tun}. \quad (1)$$

The Hamiltonian describing the leads is written as:

$$H_{leads} = \sum_{k\sigma} \epsilon_k^L a_{k\sigma}^\dagger a_{k\sigma} + \sum_{p\sigma} \epsilon_p^R b_{p\sigma}^\dagger b_{p\sigma}. \quad (2)$$

The impurity Hamiltonian is:

$$H_{imp} = \epsilon_c \sum_{\sigma} c_{\sigma}^\dagger c_{\sigma} + E_c n_{\uparrow} n_{\downarrow}, \quad (3)$$

and the tunneling term is:

$$H_{tun} = \sum_{k\sigma} (T_{Lk} c_{\sigma}^\dagger a_{k\sigma} + H.c.) + \sum_{p\sigma} (T_{Rp} b_{p\sigma}^\dagger c_{\sigma} + H.c.). \quad (4)$$

The Hamiltonian is expressed in terms of annihilation(creation) operators $a_{k\sigma}$ for the emitter, $b_{p\sigma}$ for the collector and c_{σ} for the impurity with $k(p)$ the corresponding quasimomenta and

$\sigma = \uparrow, \downarrow$ is the spin index. ϵ_k^L and ϵ_p^R are the single-particle energies in the emitter and the collector leads, respectively. E_c is the Coulomb repulsion between electrons with opposite spins. The single-electron energies are measured from the corresponding Fermi levels μ_L and μ_R in the emitter and collector, and the dc bias is $\mu_L - \mu_R = eV$. The resonant level energy is $\epsilon_c = \epsilon_c^0 + \alpha eV$, where ϵ_c^0 is the bare resonant level energy and α measures the portion of the voltage drop on the localized center. The particle-number operator is $n_\sigma = c_\sigma^\dagger c_\sigma$. In Eqn. (4) for the tunneling Hamiltonian, T_{Lk} and T_{Rp} are the tunneling matrix elements. Note that they depend on the impurity position in the junction. We assume that the impurities are randomly distributed in the junction barrier and their resonant levels are uniformly distributed in energy.

First we calculate the impurity's Green's function. To correctly account for the non-equilibrium nature of the system we apply the Keldysh technique [7]. In this technique one introduces the retarded (advanced) and distribution Green's functions. We further assume that the relaxation processes in the leads are much faster than in the impurity. Thus, we can consider the leads as equilibrium systems and the corresponding Green's functions are given by the usual expressions for a non-interacting equilibrium electron systems [7]. Here we give only the final expressions for the impurity's Green's functions (for details on the derivation see [8]). The retarded Green's function is obtained in the form

$$G_r = \frac{\omega - \tilde{\epsilon}_{c\sigma} - \Sigma_0 - \Sigma_1}{(\omega - \epsilon_c - \Sigma_0)(\omega - \epsilon_c - \Sigma_0 - \Sigma_1) - E_c(\omega - \epsilon_c - \Sigma_0 - \Sigma_2)}, \quad (5)$$

where the analytical continuation $\omega \longrightarrow \omega + i0^+$ is used. The self-energy parts in Eqn. (5) are given by

$$\Sigma_0(\omega) = \sum_{k,i=L,R} \frac{|T_{ik}|^2}{\omega - \epsilon_k^i}, \quad (6)$$

$$\Sigma_1(\omega) = \sum_{k,i=L,R} |T_{ik}|^2 \left[\frac{1}{\omega - \epsilon_{c-\sigma} - \epsilon_{c\sigma} + \epsilon_k^i} + \frac{1}{\omega + \epsilon_{c-\sigma} - \epsilon_{c\sigma} - \epsilon_k^i} \right], \quad (7)$$

$$\Sigma_2(\omega) = \sum_{k,i=L,R} |T_{ik}|^2 f(\epsilon_k^i) \left[\frac{1}{\omega + \epsilon_{c-\sigma} - \epsilon_{c\sigma} - \epsilon_k^i} + \frac{1}{\omega - \epsilon_{c-\sigma} - \epsilon_{c\sigma} + \epsilon_k^i} \right], \quad (8)$$

where $f(\epsilon_k^i)$ is the Fermi-Dirac distribution function for the electrons in the leads. We have used the following notations: $\epsilon_{c\sigma} = \epsilon_c + E_c < n_{-\sigma} >$ and $\tilde{\epsilon}_{c\sigma} = \epsilon_c + E_c(1 - < n_{-\sigma} >)$. This Green's functions describes two levels for the impurity electrons - a lower, resonant level with energy ϵ_c and the upper level with energy $\epsilon_c + E_c$.

The distribution Green's function is calculated under the assumption that the transient processes after the switching-on the dc bias have decayed and the result is

$$G_{<}(\omega) = - \frac{\sum_k |T_{Lk}|^2 A_{<}(k, \omega) + \sum_p |T_{Rp}|^2 B_{<}(p, \omega)}{\sum_k |T_{Lk}|^2 (A_r(k, \omega) - A_a(k, \omega)) + \sum_p |T_{Rp}|^2 (B_r(p, \omega) - B_a(p, \omega))} \times (G_r(\omega) - G_a(\omega)), \quad (9)$$

where $A_{r,a,<}(B_{r,a,<})$ are the retarded, advanced, and distribution Green's functions in the left (right) lead.

The average number of impurity electrons is calculated by solving the following equation

$$n = - \int \frac{d\omega}{2\pi} \text{Im} G_{<}(\omega) \quad (10)$$

(we assume $< n_{\sigma} > = < n_{-\sigma} > = n$).

It should be mentioned ([9] and references therein) that the Green's function formalism presented here is valid only for temperatures higher than the characteristic temperature for this problem - the Kondo temperature T_K .

Next we calculate the current through the impurity. In a steady-state it is given by

$$I(\epsilon_c) = ie \int \frac{d\omega}{2\pi} \frac{2\gamma_L(\omega)\gamma_R(\omega)}{\gamma_L(\omega) + \gamma_R(\omega)} (f_L(\omega) - f_R(\omega)) (G_r(\omega) - G_a(\omega)), \quad (11)$$

where

$$\gamma_L(\omega) = \pi \sum_k |T_{Lk}|^2 \delta(\omega - \epsilon_k^L), \quad \gamma_R(\omega) = \pi \sum_p |T_{Rp}|^2 \delta(\omega - \epsilon_p^R) \quad (12)$$

are the elastic widths of the impurity level due to tunneling through the left (right) barrier, respectively. We take broad, flat density of states for the leads' electrons and in the following $\gamma_L(\omega)$ and $\gamma_R(\omega)$ are assumed to be constants, γ_L and γ_R , independent of energy.

Now we compare our treatment with the work of Glazman and Matveev [6]. Their results can be obtained from ours by approximating the well electrons Green's function (Eqn. (5)) with the corresponding expression for an isolated one-center Hubbard model [10] *i.e.* one has to set all the self-energies $\Sigma_i(\omega)$, $i = 0, 2$ (Eqns. (6-8)) to zero. This approach neglects the virtual tunnel processes and it is justifiable when the temperature T is much larger than the elastic level width $\gamma = \gamma_L + \gamma_R$. With this approximation the integral equation for the average number of well electrons (Eqn. 10) reduces to an algebraic one whose solution coincides with Eqn. 6 in Ref. 6. Similarly, formula (11) for the current gives the simple analytical expression Eqn. 8 in Ref. 6.

To obtain the current through the junction we must integrate over the position of the impurity and to average over the energies of the impurity levels. If we denote the position of the impurity, relative to the left lead, by x then γ_L and γ_R depend exponentially on x

$$\gamma_L = \gamma_0 \exp\left(-\frac{2x}{\xi}\right), \quad \gamma_R = \gamma_0 \exp\left(-\frac{2(d-x)}{\xi}\right), \quad (13)$$

where d is the width of the tunnel junction and ξ is the impurity localization length. In a first approximation the coefficient γ_0 can be considered independent on x . One can show that most significant contribution to the current through the junction give the impurities which are close to its middle - $x = d/2$. Therefore, we simplify the calculation by taking $x = d/2$ in Eqn. (13) and discarding the impurities which are far from this optimal position. With this approximation the current through the junction is given by

$$I = Sd \int d\epsilon_c g(\epsilon_c) I(\epsilon_c) \quad (14)$$

where S is the area of the junction and $g(\epsilon_c)$ is the density of impurity states. In further calculations we take $g(\epsilon_c)$ to be a constant. In Eqn. (14) the integration is over all impurities which give non-zero contribution to the current.

In Fig. 1 we show the current through the impurities as a function of the energy of the impurity level for: a) $V = 2.2E_c$; b) $V = 0.6E_c$ and for $T = 0.08E_c$ ($\gamma_0 = 0.02E_c$). We have set $\mu_R = 0$ since the results are independent on the value of the right chemical potential. The current is almost zero when both impurity levels - the resonant and the upper level, are well below the right chemical potential or well above the left chemical potential. In the former case $n = 1$ - there are 2 electrons on the impurity and in the latter $n \approx 0$. For $V > E_c$ the current is maximal when both impurity levels are between the left and right chemical potentials - there is approximately 1 electron on the impurity. The left "shoulder" in $I(\epsilon_c)$ dependence for $V = 2.2E_c$ (Fig. 1 a) corresponds to impurities for which $n \approx 1/3$ and the right "shoulder" is due to impurities with $n \approx 2/3$. For $V < E_c$ there are two peaks in the $I(\epsilon_c)$ dependence (Fig. 1 b). The lower comes from tunneling through the upper level for impurities deep below μ_R (for them only the upper level is above μ_R). The upper peak is due to impurities whose resonant level is above μ_R and the upper level is above μ_L . In this case the tunneling current flows predominantly through the resonant level. In Fig. 1 c we show $I(\epsilon_c)$ dependence for $T = 0.9E_c$ and $V = 0.6E_c$. It is evident that for temperatures comparable with E_c all charging effects are smeared out by the thermal fluctuations.

In Fig. 2 we present the I-V characteristic of the tunnel junction, calculated for: a) $T = 0.002E_c$ and b) $T = 0.9E_c$. In the former case the current is linear in V both for low voltage $V < E_c$ and for $V > E_c$ and changes slope at $V = E_c$ - the slope diminishes for $V > E_c$. This behaviour can qualitatively be understood by the following considerations. With increasing V more impurities are involved in the transport through the junction. As V increases to E_c the current through the junction increases significantly since it flows through impurities which give maximal current (Fig. 1). Increasing V above E_c includes impurities with resonant levels close to μ_L - for them the current is rapidly decreasing function of ϵ_c (Fig. 1). We must point out that for temperatures $T < 0.5E_c$ the I-V characteristic

is practically independent on the temperature which again is a signature of the charging effects.

The I-V characteristic at $T = 0.9E_c$ (Fig. 2b) shows ohmic behavior of the tunnel junction. The current is linear in V for every voltage - the charging effects of the resonant tunneling are fully masked by the thermal fluctuations.

In this work we have approximated the tunneling matrix elements to be independent on energy (equivalently, on the applied *dc* voltage). One may speculate that taking $T_{L(R)}$ to be increasing functions of V and ϵ_c (softening of the barrier with increasing energy) will give the experimentally observed I-V characteristics [3] - for V exceeding E_c the slope of the $I(V)$ dependence increases.

In summary, in the present paper the phenomenon of resonant tunneling through a tunnel junction containing impurity states in the barrier region has been studied with the Coulomb repulsion between electrons on the impurity taken into account. The I-V characteristic at temperature $T \ll E_c$ is linear in V both for $V < E_c$ and for $V > E_c$ and its slope diminishes at $V = E_c$. The tunnel junction has ohmic-like I-V characteristic for temperatures of the order of the charging energy when the charging effect is smeared out by the thermal fluctuations.

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REFERENCES

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- [1] A. B. Fowler, G. L. Timp, J. J. Wainer, and R. A. Webb, Phys. Rev. Lett. **57**, 138 (1986).
- [2] M. Naito and M. R. Beasley, Phys. Rev. B **35**, 2548 (1987).
- [3] L. I. Glazman and K. A. Matveev, Zh. Eksp. Teor. Fiz. **94**, 332 (1988) [Sov. Phys. JETP **67**, 1276 (1988)].
- [4] Y. Xu, A. Matsuda, and M. R. Beasley, Phys. Rev. B **42**, 1492 (1990).
- [5] D. Ephron, Y. Xu, and M. R. Beasley, Phys. Rev. Lett. **69**, 3112 (1992).
- [6] L. I. Glazman and K. A. Matveev, Pis'ma Zh. Eksp. Teor. Fiz. **48**, 403 (1988); **49**, 570 (1989).
- [7] L. D. Landau and E. M. Lifshitz, *Physical Kinetics* (Pergamon Press, Oxford, 1981), Chapter X.
- [8] T. Ivanov, D. Marvakov, V. Valtchinov, and L. T. Wille, Phys. Rev. B **48**, 4679 (1993).
- [9] C. Lacroix, J. Phys. F **11**, 2389 (1981).
- [10] J. Hubbard, Proc. Roy. Soc. London A **276**, 238 (1963).

FIGURES

FIG. 1. Current (in arb. units) through the impurity centers as a function of their energy ϵ_c for $T = 0.08E_c$: a) $V = 2.2E_c$ (the dotted line), b) $V = 0.6E_c$ (the solid line), and c) for $T = 0.9E_c$ and $V = 0.6E_c$ (the dashed line).

FIG. 2. I-V characteristics of the tunnel junction for: a) $T = 0.002E_c$ (the solid line), and b) $T = 0.9E_c$ (the dashed line). The current is normalized to $I(E_c)$.